



CNES detector development for scientific space missions: status and roadmap for infrared detectors

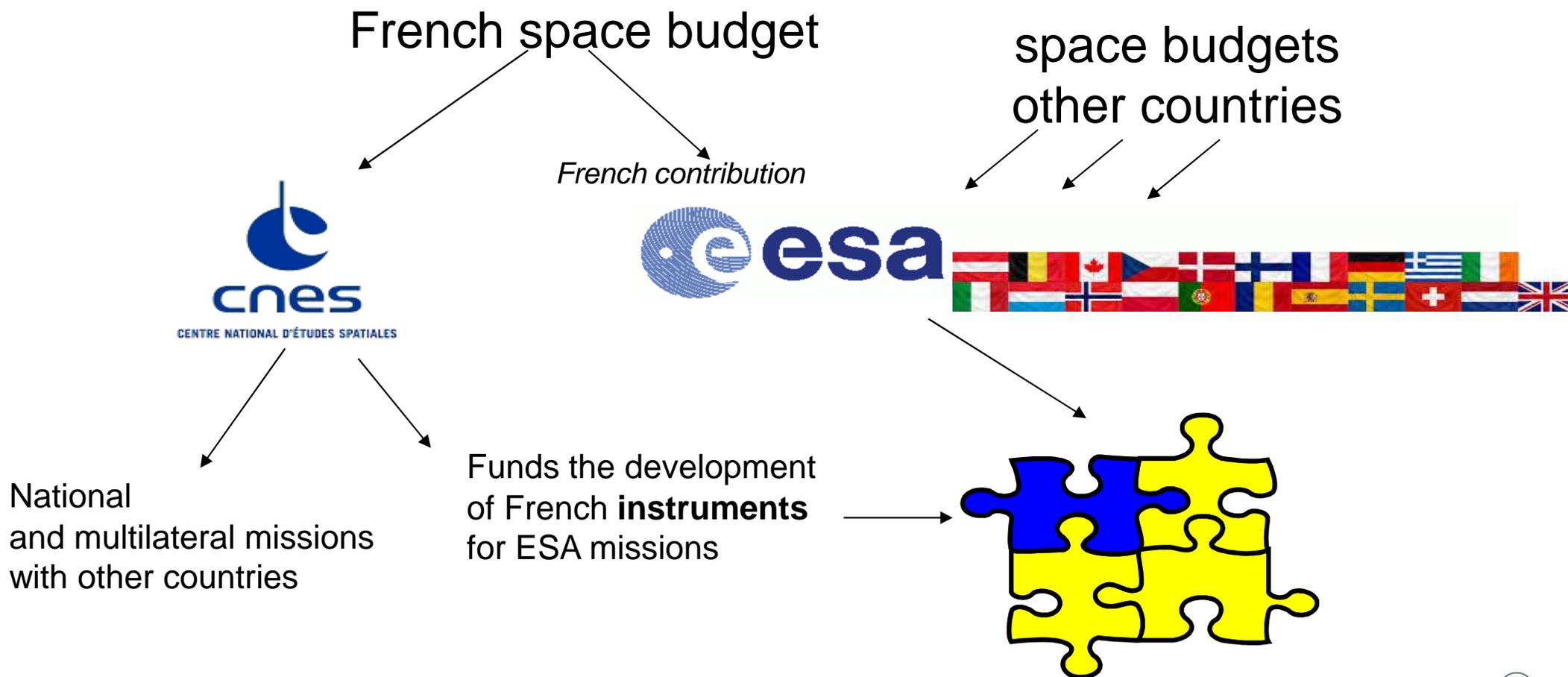
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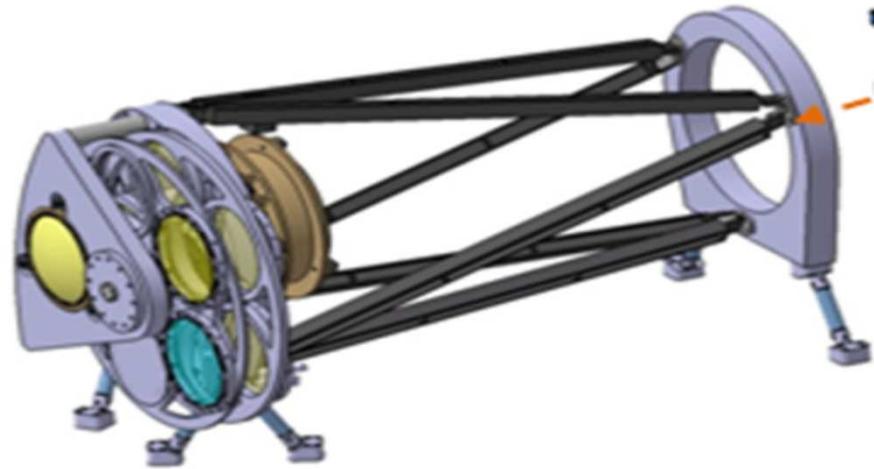
^b Commissariat à l'Energie Atomique

^cSOFRADIR

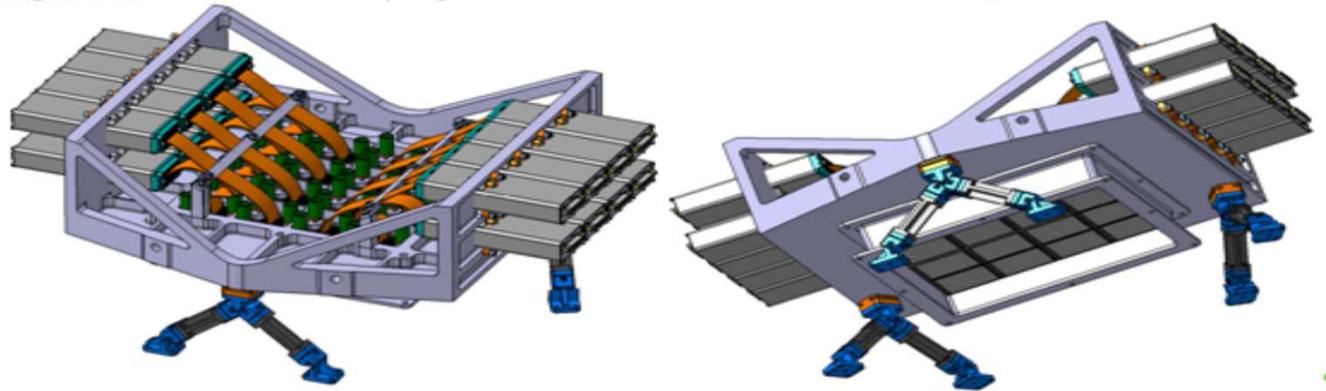
Space projects in Europe



Euclid



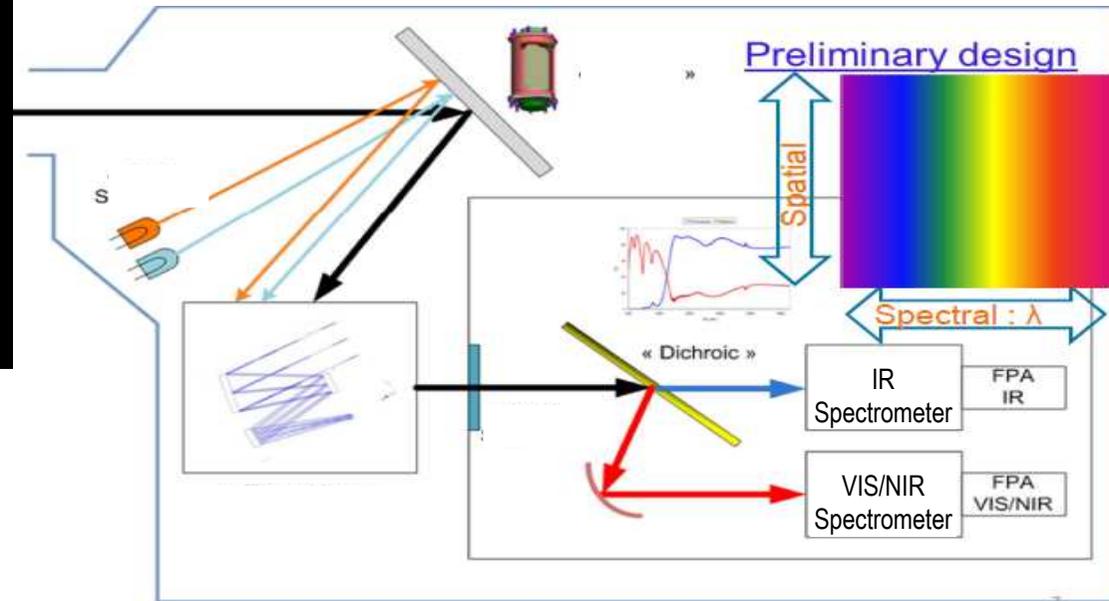
Cosmic vision M2
CDR passed
Expected Launch 2020

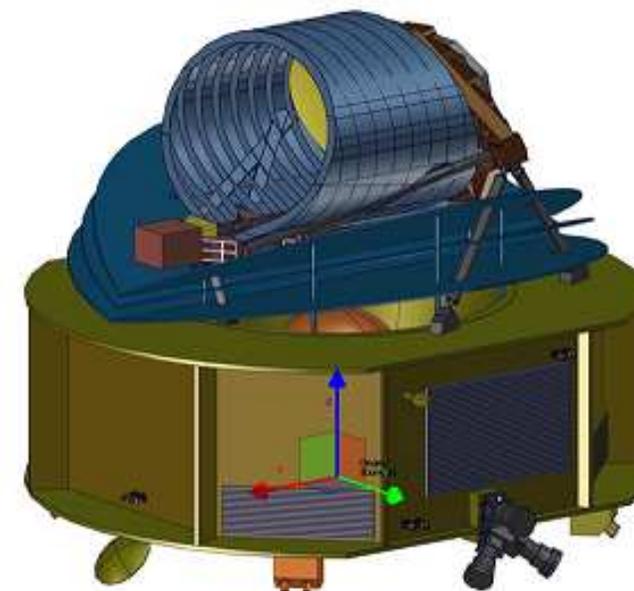


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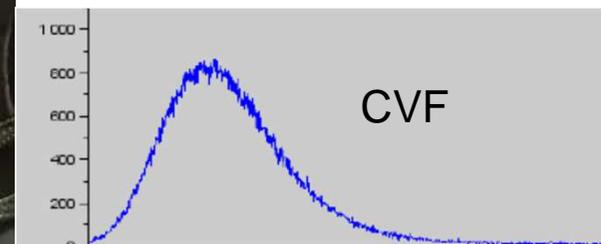
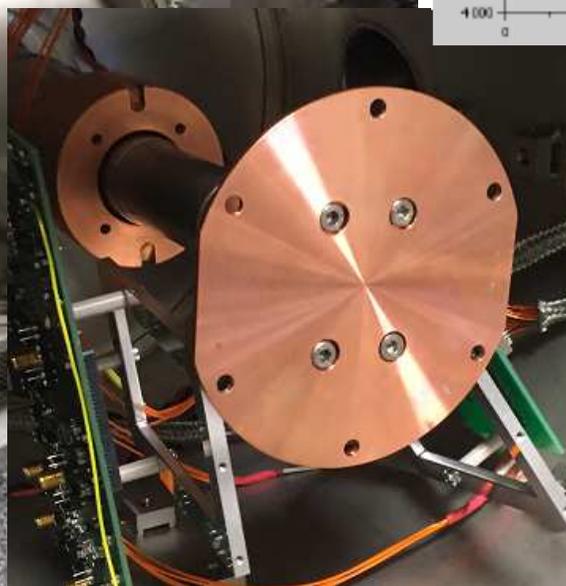
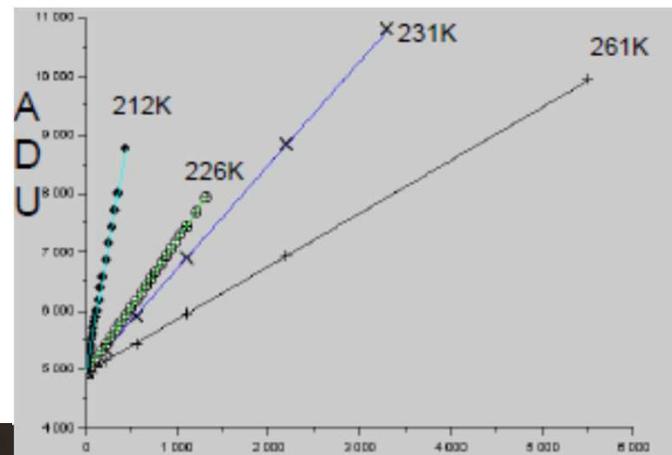
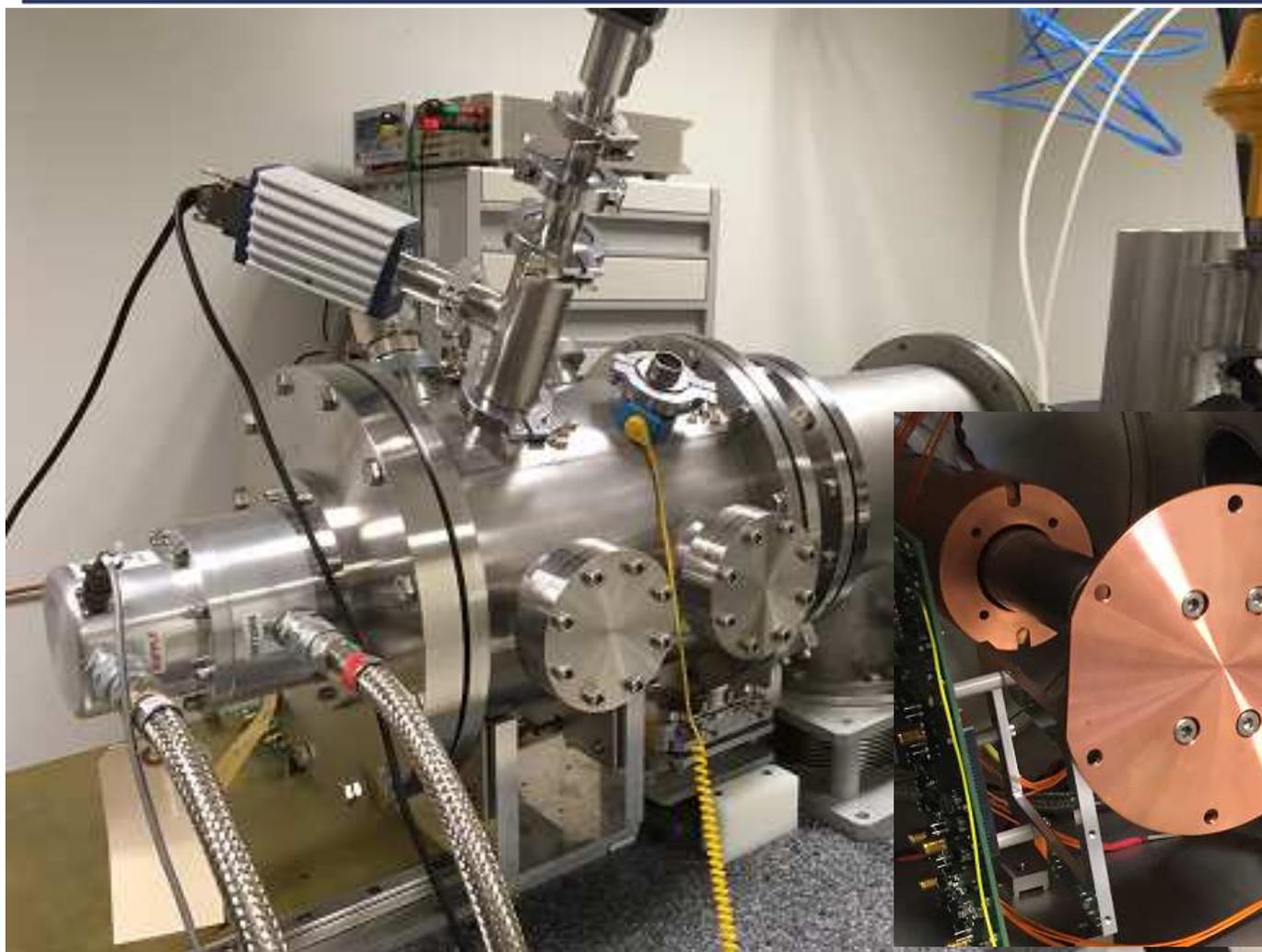
Cosmic vision L1
Phase B ongoing
Expected Launch 2022



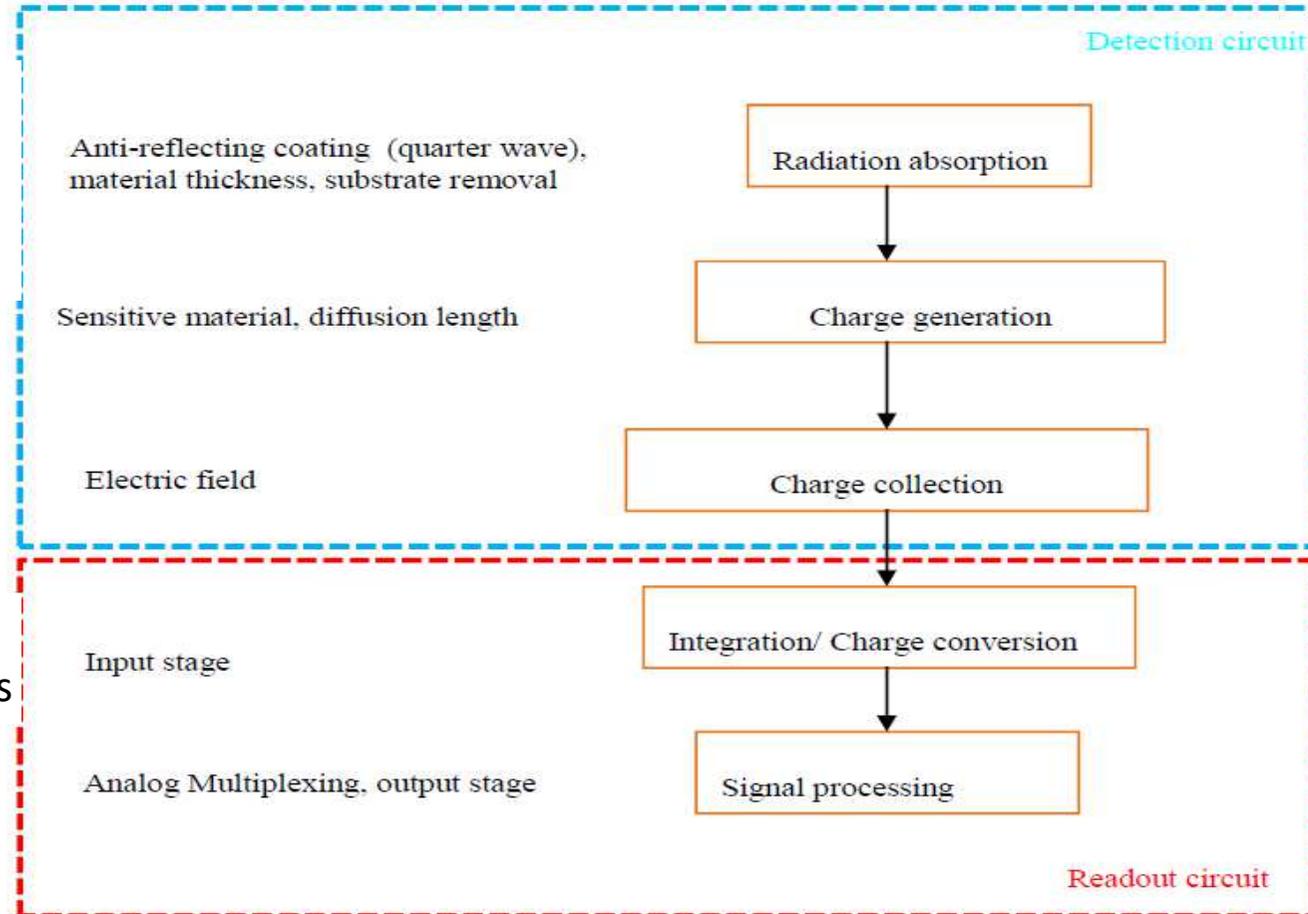
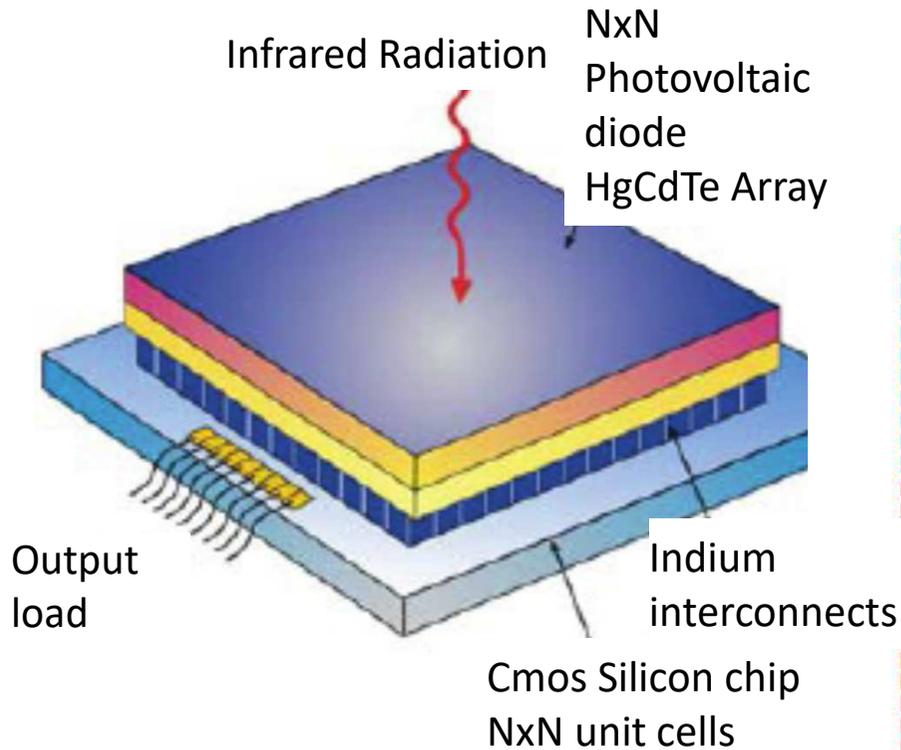


**Cosmic vision : M4 candidate currently
in phase A
Expected Launch 2026**

Characterisation at CNES laboratories



The HgCdTe Infrared Detector



Key technologies of HgCdTe infrared detectors for scientific application

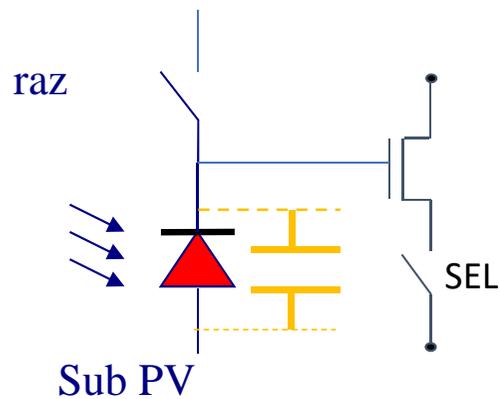


- **Large format detectors from 1k² to 2k² arrays : need to overcome strong technological limitations**
- **Low readout noise detectors**
- A specific input stage for very low flux : SFD (Source Follower per detector) : Very low flux, very low power, low noise, glow free
- Another solution : APD (Avalanche Photodiode) technology: allows a signal gain at diode level (demonstrated for n/p diode)
- **Photodiode p/n technology: is necessary to achieve low dark current and allows good signal to noise ratio performance**

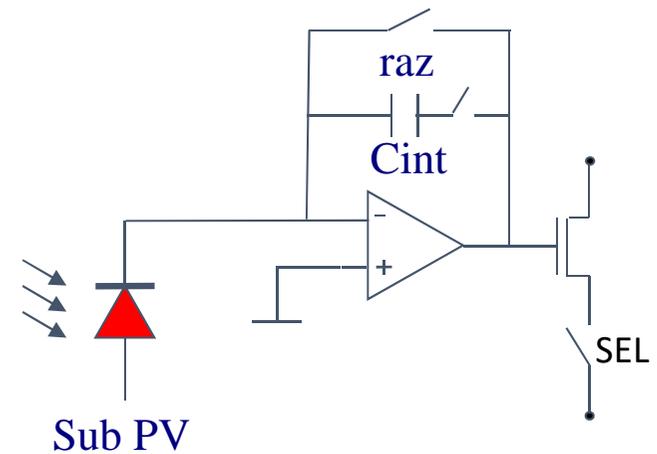
➡ **CNES developments to prepare future space missions**

ReadOut Circuit (ROIC) input stages

SFD (Source Follower Detector) Integration on detector node



CTIA (Capacitive Transimpedance Amplifier)



ReadOut Circuits (ROIC) input stages



Performance	SFD	CTIA	Comments
Noise without CDS	15-20e ⁻ rms typ.	30-150 e ⁻ rms (lower limit)	The noise figure can be lowered with CDS or multiple (and non-destructive) readout. Few e ⁻ rms noise can be reached with SFD
Flux range	0.01 e ⁻ /s/pixel to <10 ⁴ e ⁻ /s/pixel	few 10 ⁴ e ⁻ /s/pixel to few 10 ⁸ e ⁻ /s/pixel typ.	
Charge capacity	< 10 ⁵ e ⁻ typ.	10 ⁵ e ⁻ to few 10 ⁶ e ⁻ typ.	Charge capacity depends on the photodiode wavelength detection range for SFD
Readout frequency	up to 500 kHz	up to 20 MHz	SFD ROIC drive an output capacitance of ~few pF, whereas CTIA ROIC can drive ~100 pF capacitance
Power dissipation	1 mW typ.	50-150mW	

SFD vs CTIA input stage



Main intrinsic limitation of the SFD input stage :

- Relatively small integration capacity (associated with a large potential offset dispersion) which limits its use for “medium input fluxes”.
- Low frequency readout/poor capability to drive large impedance (needs for intermediate electronics stage at low temperature)
- Electronics operating point to be tune finely

Main limitation of the CTIA input stage :

- Compatibility with input fluxes in the range few 10^2 to 10^3 e-/s/pixel?
- Glow (self-parasitic light) effect from the ROIC itself and/or current leakage effects can affect the performance, either by degrading the noise budget (parasitic flux), or the linearity at very low level (floor/threshold effect,...).

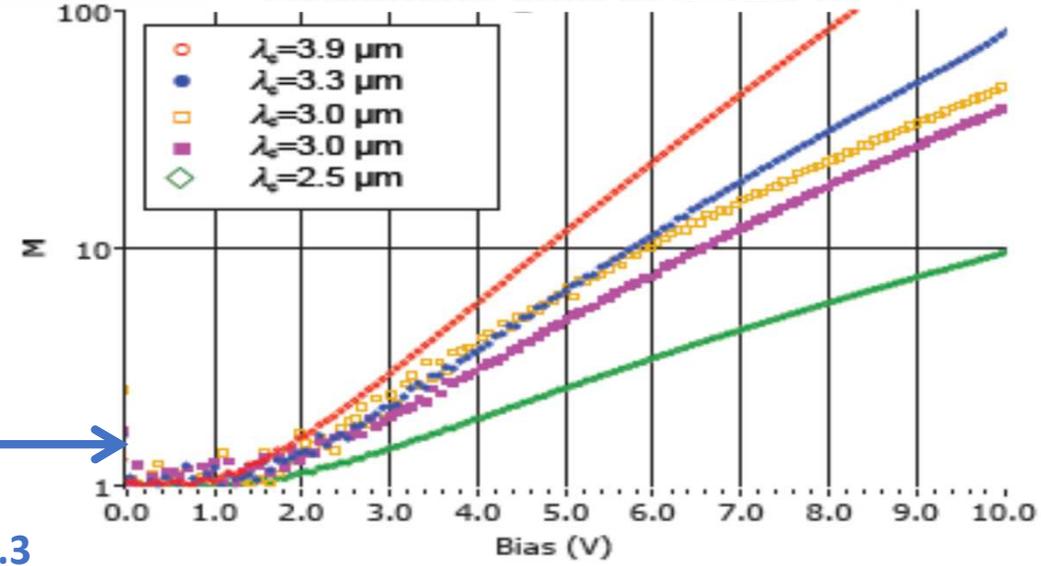
What about ADP+CTIA ?



	Classical Photodiode	APD
Signal	$N \epsilon$	$N \epsilon \cdot M$
Noise	$\sqrt{N \epsilon}$	$\sqrt{N \epsilon \cdot M^2 \cdot F(M)}$

$$RSB = \frac{N_{ph} M}{\sqrt{RON + N_{ph} M^2 F}}$$

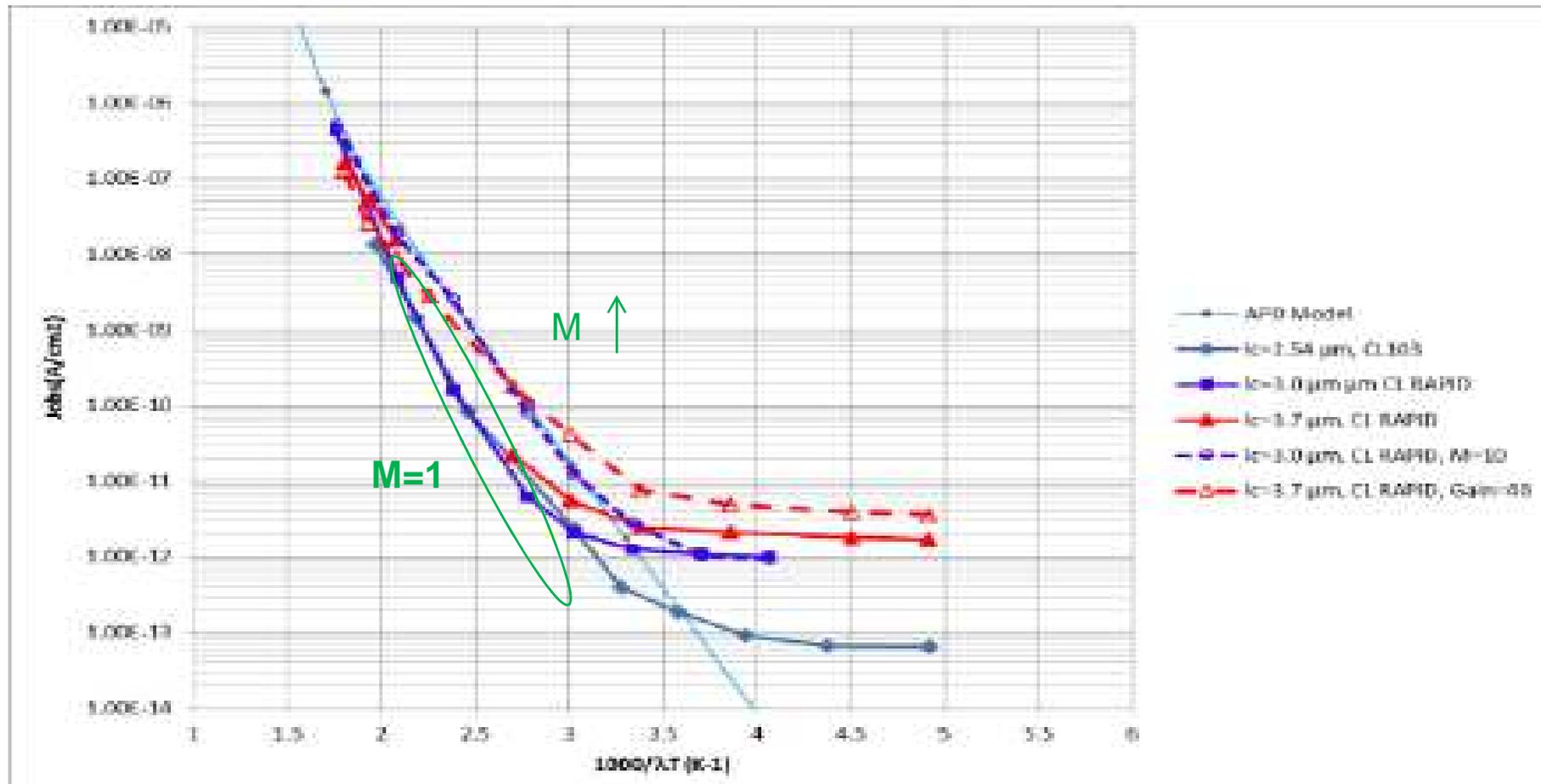
M →
F(M)~1.2-1.3



Still open points to be addressed in order to reach a good performance:

- CTIA parasitic current of the order of 50-100 electron/s: too high wrt requirements (~< 1 electron/s)
- n/p APDs are difficult to use for cutoff wavelength below ~3μm
 - the smaller is the wavelength the higher is the bias needed
- dark current signal levels are still higher than the requirement (G-R dark currents)

Dark current contribution in APD



Log scale

Flux (e^-)

Qmax limit

DI based ROI

Qmin.noise limit

CTIA based ROIC

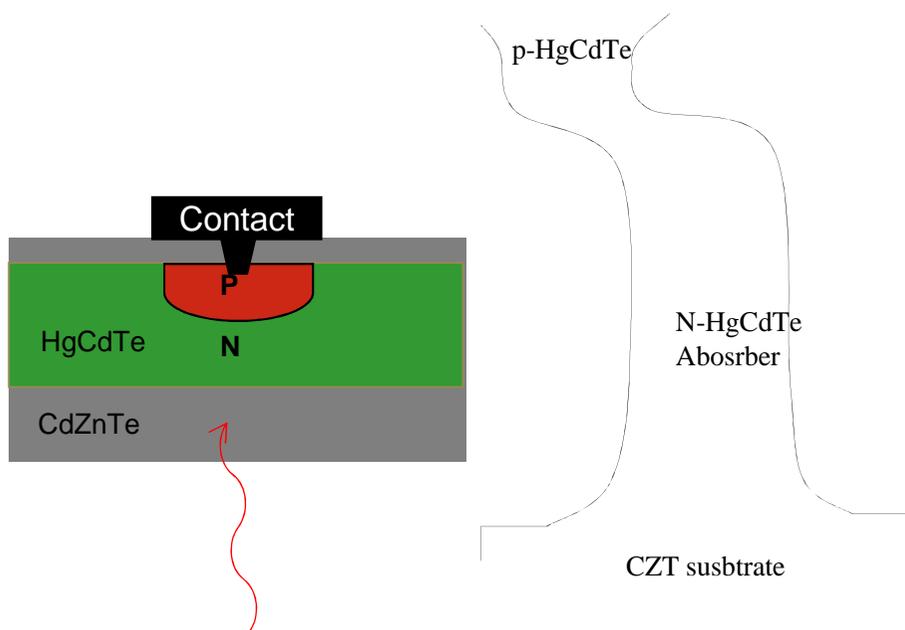
Deep Imaging
Large Field of View

SFD based ROIC

Frame frequency (Hz)

APD improvement

Planetary exploration



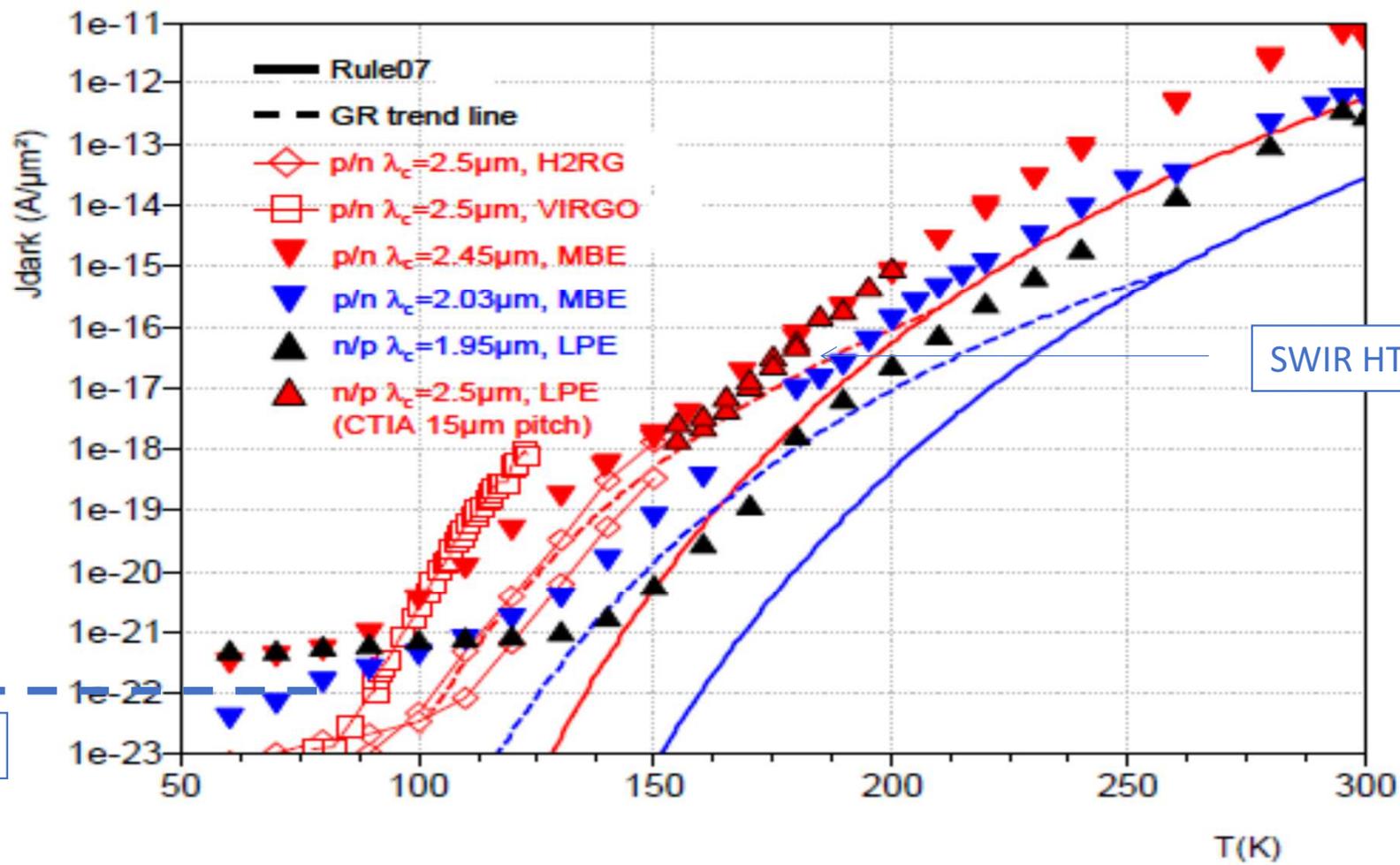
Dark signal $< 0.1 \text{ é/s}$ needs:

- High quality HgCdTe material
- Optimized junction process
 - Graded junction
 - control of the doping level



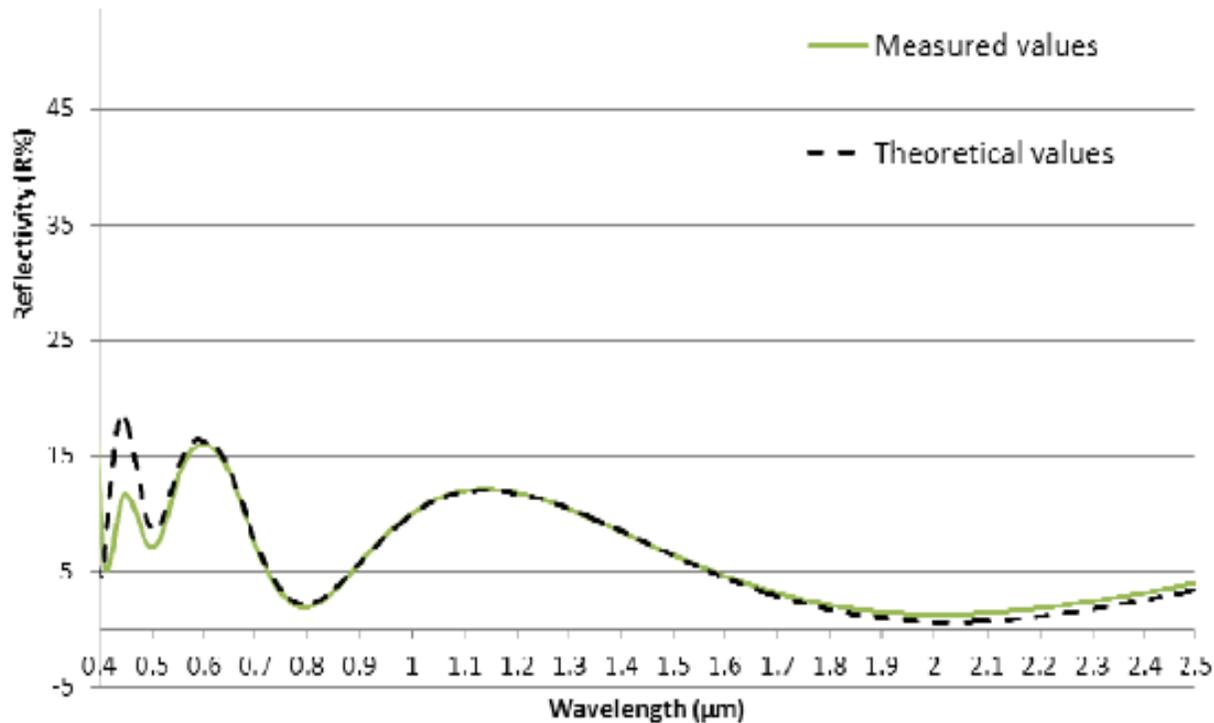
- **CNES developments :**
 - **NIR/SWIR bands (cutoff wavelength $> 2 \mu\text{m}$ @ 77K), LPE process**
 - Joint effort with Earth observation mission (FPA temperature $< 150\text{K}$)
 - **LWIR bands (cutoff wavelength $\sim 12 \mu\text{m}$ @ 40K), LPE process**
 - Echo mission

SWIR p/n results

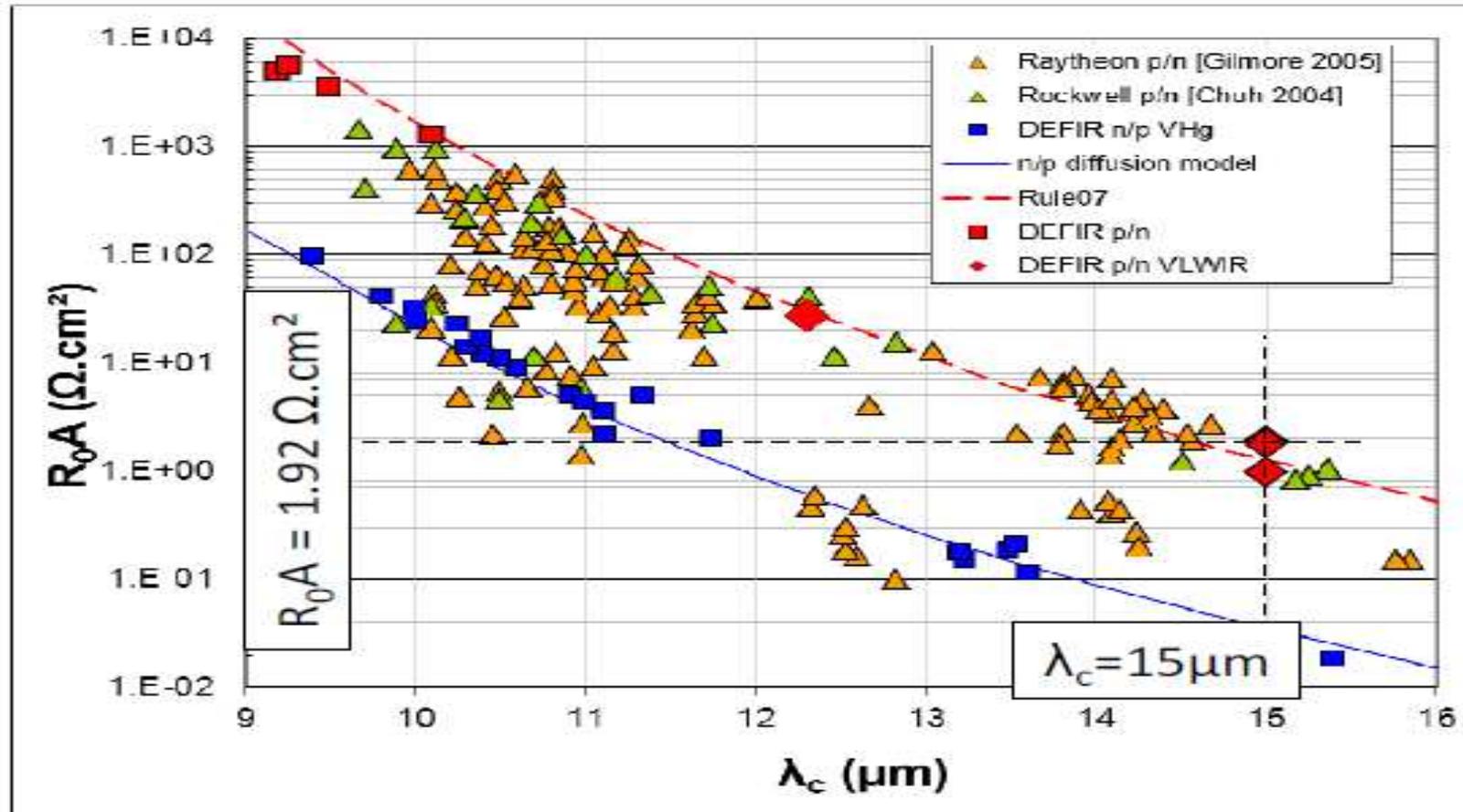


Multilayer A/R coating

- Increase of the sensitivity on a large spectral band
- ARC deposition should not impact detector performances: processes and handling are critical



LWIR p/n results



Large Format Infrared Detector Arrays

- **Main challenges are:**

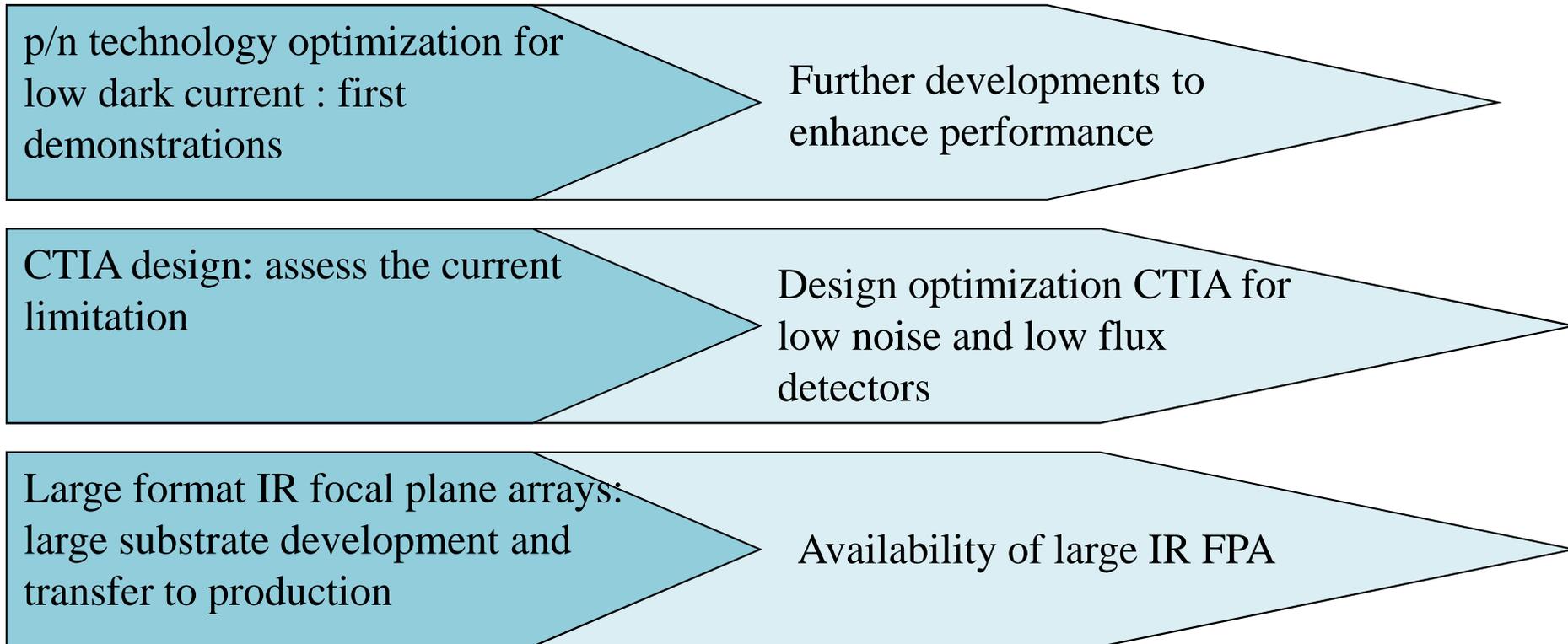
- Stitching capability of the CMOS foundry
- Large substrate growth
- Hybridization technology



- **Current developments are focusing on two main topics:**

- **Enhancement of the production capabilities** for array format of 1kx1k pixels or more
- **Large detection circuits fabrication:** Sofradir and CEA-LETI have shown excellent control of CZT ingots fabrication:
 - 3.5\" CZT substrate size is now under production
 - HgCdTe epilayer deposition is well-controlled and within the production standard
 - Photodiode processes on large substrates has been demonstrated.

Future trends and perspectives



- **ESA is currently developing a 2K² SWIR based on SFD ROIC and p/n technology**
- **Coordination and joint efforts with ESA and French Laboratories (Labex Focus) for those developments**

Acknowledgements

To ESA and Labex Focus for their partnership

**To the teams who have worked on those developments (CEA-LETI, CEA-Irfu,
Sofradir)**